

NPN Epitaxial Silicon Transistor KSC945

Features

- Audio Frequency Amplifier and High-Frequency OSC
- Complimentary to KSA733
- Collector-Base Voltage: V_{CBO} = 60 V
- High Current Gain Bandwidth Product: f_T = 300 MHz (Typical)
- Suffix "-C" Means Center Collector (1. Emitter 2. Collector 3. Base)

ABSOLUTE MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$

Symbol	Parameter	Ratings	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	٧
Ic	Collector Current	150	mA
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

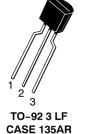
THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	250	mW
	Derate Above 25°C	2.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	500	°C/W

^{1.} PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

1. Emitter 2. Base 3. Collector 123 TO-92 3 CASE 135AN CA



MARKING DIAGRAM

AC945Y YWW

A = Assembly Site
C945Y = Specific Device Code
Y = Year of Production
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
KSC945YBU	TO-92 3 (Pb-Free)	10,000 Units / Bulk
KSC945CYTA	TO-92 3 LF (Pb-Free)	2,000 Units / FNFLD
KSC945YTA	TO-92 3 LF (Pb-Free)	2,000 Units / FNFLD

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	60	_	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	50	_	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μA, I _C = 0	5	-	-	V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 40 V, I _E = 0	-	-	0.1	μΑ
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 3 V, I _C = 0	-	-	0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} = 6 V, I _C = 1.0 mA	120	-	240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 100 mA, I _B = 10 mA	-	0.15	0.30	V
f _T	Current Gain Bandwidth Product	V _{CE} = 6 V, I _C = 10 mA	-	300	-	MHz
C _{ob}	Output Capacitance	V _{CB} = 6 V, I _E = 0, f = 1 MHz	-	2.5	-	pF
NF	Noise Figure	$V_{CE} = 6 \text{ V}, I_{C} = 0.5 \text{ mA}, f = 1 \text{ kHz}, R_{S} = 500 \Omega$	_	4.0	-	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

KSC945

TYPICAL CHARACTERISTICS

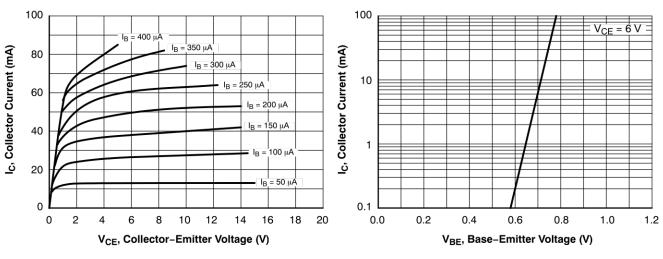


Figure 1. Static Characteristic

Figure 2. Transfer Characteristic

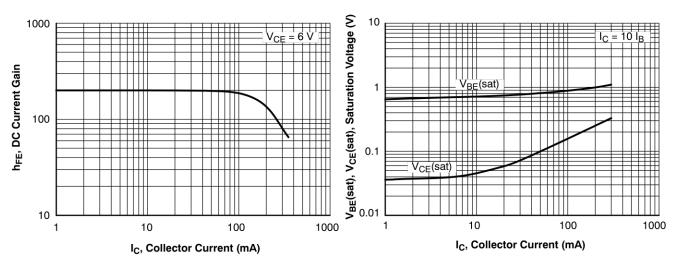


Figure 3. DC Current Gain

Figure 4. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage

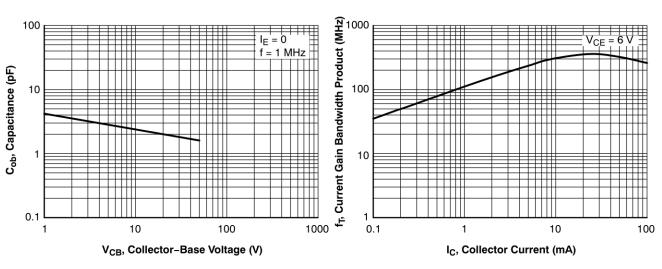


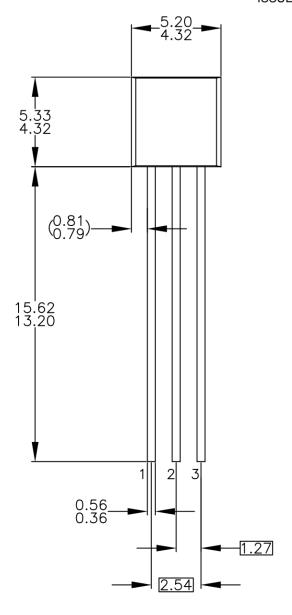
Figure 5. Output Capacitance

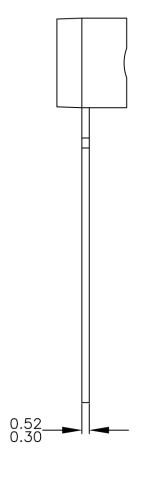
Figure 6. Current Gain Bandwidth Product



TO-92 3 4.825x4.76 CASE 135AN **ISSUE O**

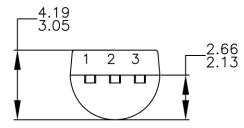
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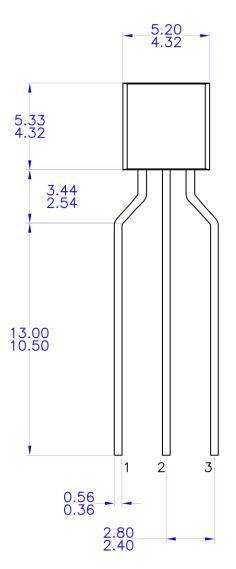
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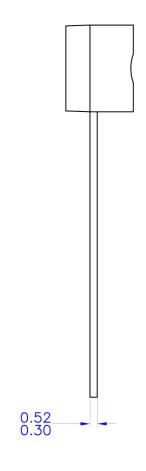
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TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

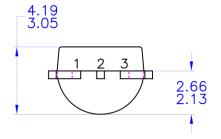
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